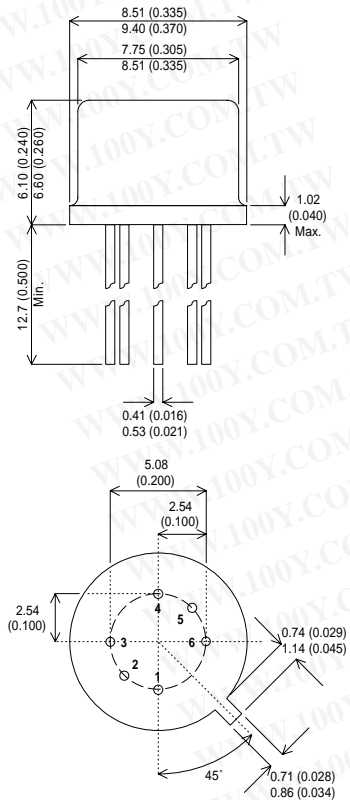


MECHANICAL DATA

Dimensions in mm (inches)



DUAL NPN PLANAR TRANSISTORS IN TO77 PACKAGE

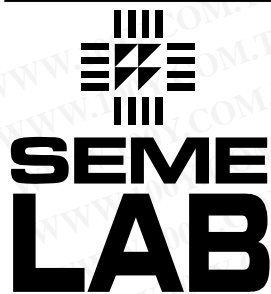
TO-77 PACKAGE

PIN 1 – Collector 1 PIN 4 – Emitter 2
 PIN 2 – Base 1 PIN 5 – Base 2
 PIN 3 – Emitter 1 PIN 6 – Collector 2

ABSOLUTE MAXIMUM RATINGS

($T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

		EACH SIDE	TOTAL DEVICE
V_{CBO}	Collector – Base Voltage	45V	
V_{CEO}	Collector – Emitter Voltage ¹	45V	
V_{EBO}	Emitter – Base Voltage	6V	
I_C	Continuous Collector Current	30	
P_D	Total Device Dissipation	$T_{AMB} = 25^{\circ}\text{C}$	300mW
		Derate above 25°C	1.72mW / $^{\circ}\text{C}$
P_D	Total Device Dissipation	$T_C = 25^{\circ}\text{C}$	500mW
		Derate above 25°C	2.86W / $^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-65 to 200°C	
T_L	Lead temperature (Soldering, 10 sec.)	300 $^{\circ}\text{C}$	



勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

2N2913
 2N2915
 2N2917

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C unless otherwise stated)

Parameter	Test Conditions ¹	Min.	Typ.	Max.	Unit		
INDIVIDUAL TRANSISTOR CHARACTERISTICS							
V _{(BR)CBO}	Collector – Base Breakdown Voltage	I _C = 10μA	I _E = 0	45	V		
V _{(BR)CEO*}	Collector – Emitter Breakdown Voltage	I _C = 10mA	I _B = 0	45			
V _{(BR)EBO}	Emitter – Base Breakdown Voltage	I _E = 10μA	I _C = 0	6			
I _{CBO}	Collector Cut-off Current	V _{CB} = 45V	I _E = 0		10	nA	
			T _A = 150°C		10	μA	
I _{CEO}	Collector Cut-off Current	V _{CE} = 5V	I _B = 0		2	nA	
I _{EBO}	Emitter Cut-off Current	V _{EB} = 5V	I _C = 0		2		
h _{FE}	DC Current Gain	V _{CE} = 5V	I _C = 10μA		60	240	
				T _A = -55°C	15		
		V _{CE} = 5V	I _C = 100μA	100			
		V _{CE} = 5V	I _C = 1mA	150			
V _{BE}	Base – Emitter Voltage	V _{CE} = 5V	I _C = 100μA		0.70	V	
V _{CE(sat)}	Collector – Emitter Saturation Voltage	I _B = 100μA	I _C = 1mA		0.35		
h _{ib}	Small Signal Common – Base Input Impedance	V _{CB} = 5V	I _C = 1mA		25	32	
		f = 1kHz					
h _{ob}	Small Signal Common – Base Output Admittance	V _{CB} = 5V	I _C = 1mA			1	μmho
		f = 1kHz					
h _{fe}	Small Signal Common – Base Current Gain	V _{CE} = 5V	I _C = 500μA		3		—
		f = 20MHz					
C _{obo}	Common – Base Open Circuit Output Capacitance	V _{CB} = 5V	I _E = 0			6	pF
		f = 140kHz to 1MHz					

* Pulse Test: t_p = 300μs, δ ≤ 1%.

Parameter	Test Conditions	2N2915			2N2917			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
TRANSISTOR MATCHING CHARACTERISTICS								
h _{FE1}	Static Forward Current	V _{CE} = 5V	I _C = 100μA					—
h _{FE2}	Gain Balance Ratio	See Note 2.		0.9	1	0.8	1	
V _{BE1} - V _{BE2}	Base – Emitter Voltage Differential	V _{CE} = 5V	I _C = 100μA		3		5	mV
		V _{CE} = 5V	I _C = 10μA to 1mA		5		10	
Δ(V _{BE1} - V _{BE2})ΔT _A	Base – Emitter Voltage Differential Change With Temperature	V _{CE} = 5V	I _C = 100μA		0.8		1.6	mV
		T _{A1} = 25°C	T _{A2} = -55°C					
		V _{CE} = 5V	I _C = 100μA		1		2	
		T _{A1} = 25°C	T _{A2} = 125°C					